

material operative under field effect to conduct current between the source semiconductor material and the drain semiconductor material;

a conductive gate structure configured to enable provision of a field to the channel semiconductor material;

*E'* a gate oxide layer disposed between the conductive gate structure and the channel semiconductor material;

said conductive gate structure comprising doped polysilicon contacting the oxide layer  
*112 let* and [metal disposed coextensively over the doped polysilicon];

an insulating layer disposed over said gate structure; and

*112 let* metallization over said insulating layer, [the metallization contacting the gate structure through said insulating layer].

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